

TPS92560

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# SIMPLE LED DRIVER FOR MR16 AND AR111 APPLICATIONS

Check for Samples: TPS92560

## FEATURES

- Controlled peak input current to prevent overstressing of the electronic transformer
- Allows either step-up or step-up/down
   operation
- Compatible to generic electronic transformers
- Compatible to magnetic transformers and DC power supplies
- · Integrated active low-side input rectifiers
- Compact and simple circuit
- >85% efficiency (12VDC input)
- Power factor > 0.9 (full load with AC input)
- Hysteretic control scheme
- Output Over-Voltage Protection
- Over-temperature Shutdown
- 10-pin mini SOIC package with exposed pad

### APPLICATIONS

- MR16/AR111 LED lamps
- Lighting system using electronic transformer
- General lighting systems that require a boost / SEPIC LED driver

### DESCRIPTION

The TPS92560 is a simple LED driver designed to drive high power LEDs by drawing constant current from the power source. The device is ideal for MR16 and AR111 applications which need aood compatibility to DC and AC voltages and electronic transformers. The hysteretic control scheme does not need control loop compensation while providing the benefits of fast transient response and high power factor. The patent pending feedback control method allows the output power to be determined by the number of LED used without component change. The TPS92560 supports both boost and SEPIC configurations for the use of different LED modules.



Typical application circuit of the TPS92560 using boost configuration

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## TYPICAL APPLICATION

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## **TYPICAL APPLICATION (Continue)**



Typical Application Circuit of the TPS92560 using SEPIC configuration





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### **BLOCK DIAGRAM**



SVA-30207403

#### ORDERING INFORMATION

ORDER NUMBER	PACKAGE TYPE	NSC PACKAGE DRAWING	SUPPLIED AS	
TPS92560DGQ		MUCIOA	1000 Units on Tape and Reel	
TPS92560DGQR	10L MINI SOIC EXP PAD	MUC10A	4500 Units on Tape and Reel	





Package Number MUC10A

SVA-30207405

#### TERMINAL FUNCTIONS

	PIN	DESCRIPTION						
NO.	NAME	DESCRIPTION	APPLICATION INFORMATION					
1	GATE	Gate driver output pin	Connect to the Gate terminal of the low-side N-channel Power FET					
2	SRC	Gate driver return	Connect to the Source terminal of the low-side N-channel Power FET					
3	VCC	VCC regulator output	Connect 0.47µF decoupling cap from this pin to SRC pin					
4	SEN	Current sense pin	Kelvin-sense current sensing input. Should connect to the current sensing resistor, $R_{\text{SEN}}$					
5	GND	Analog ground	Reference point for current sensing.					
6	ADJ	LED current adjust pin	Connect to resistor divider from LED top voltage rail to set LED current					
7	VP	Power supply of the IC	Connect it to the LED top voltage rail (for boost) or Connect it through a diode from LED top voltage rail (for SEPIC)					
8	AC2	Power return terminal	Connect to AC or DC input terminal					
9	PGND	Power ground	Connect to system ground plane					
10	AC1	Power return terminal	Connect to AC or DC input terminal					
	PowerPAD	Thermal DAP	Connect to system ground plane for heat dissipation					

### ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

		VALUE	UNIT
	SRC, SEN, ADJ	–0.3 to 5	V
	AC1, AC2	-1 to 45	V
	VP	-0.3 to 45	V
	VCC	–0.3 to 12	V
ESD Rating	Human Body Model <sup>(2)</sup>	1.5	kV
	Storage Temperature	-65 to +150	°C
TJ	Junction Temperature	-40 to +125	°C

(1) Absolute Maximum Ratings are limits which damage to the device may occur. Operating ratings are conditions under which operation of the device is intended to be functional. For specifications and test conditions, see the electrical characteristics.

(2) The human body model is a 100 pF capacitor discharged through a 1.5 k $\Omega$  resistor into each pin.



### **RECOMMENDED OPERATING CONDITIONS**

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
VP	Supply voltage range	6.5	42	V
TJ	Junction temperature range	-40	125	°C
$\theta_{JA}$ <sup>(1)</sup>	Thermal resistance, Junction to Ambient, 0 LFPM Air Flow		48	°C/W
$\theta_{JC} \ ^{(1)}$	Thermal resistance, Junction to Case		10	°C/W

(1)  $\theta_{JA}$  and  $\theta_{JC}$  measurements are performed on JEDEC boards in accordance with JESD 51-5 and JESD 51-7

## **ELECTRICAL CHARACTERISTICS**

Specification with standard type are for  $T_A=T_J=25^{\circ}$ C only; limits in **boldface** type apply over the full Operating Junction Temperature (T<sub>J</sub>) range. Minimum and Maximum are specified through test, design or statistical correlation. Typical values represent the most likely parametric norm at  $T_J=25^{\circ}$ C, and are provided for reference purposes only. Unless otherwise stated the following conditions apply:  $V_{VP} = 12V$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY						
I <sub>IN</sub>	V <sub>IN</sub> Operating current	6.5 V < V <sub>VP</sub> < 42 V	0.7	1.4	1.95	mA
VCC REGULAT	OR					
	(4)	$I_{CC} \le 10$ mA, $C_{VCC} = 0.47 \mu$ F 12V < $V_{VP} < 42$ V	7.82	8.45	9.08	
V <sub>CC</sub>	V <sub>CC</sub> Regulated Voltage <sup>(1)</sup>	$I_{CC}$ = 10mA, $C_{VCC}$ =0.47µF $V_{VP}$ = 6.5V	5.22	5.8	6.18	V
		$I_{CC}$ = 0mA, $C_{VCC}$ =0.47µF $V_{VP}$ = 2V	1.96			
I <sub>CC-LIM</sub>	V <sub>CC</sub> Current Limit	$V_{CC} = 0V \ 6.5V < V_{VP} < 42V$	21	30	39	mA
V <sub>CC-UVLO-UPTH</sub>	V <sub>CC</sub> UVLO Upper Threshold		5.0	5.38	5.76	V
V <sub>CC-UVLO-LOTH</sub>	V <sub>CC</sub> UVLO Lower Threshold		4.63	4.98	5.33	V
V <sub>CC-UVLO-HYS</sub>	V <sub>CC</sub> UVLO Hysteresis		190	400	640	mV
MOSFET GATE	DRIVER	l			1	
V <sub>GATE-HIGH</sub>	Gate Driver Output High	w.r.t. SRC Sinking 100mA from GATE Force VCC = 8.5V	7.61	8.1	8.5	V
V <sub>GATE-LOW</sub>	Gate Driver Output Low	w.r.t. SRC Sourcing 100mA to GATE	100	180	290	mV
t <sub>RISE</sub>	V <sub>GATE</sub> Rise Time	$C_{GATE} = 1nF$ across GATE and SRC		22		ns
t <sub>FALL</sub>	V <sub>GATE</sub> Fall Time	$C_{GATE} = 1nF$ across GATE and SRC		14		ns
t <sub>RISE-PG-DELAY</sub>	V <sub>GATE</sub> Low to High Propagation Delay	C <sub>GATE</sub> = 1nF across GATE and SRC		68		ns
t <sub>FALL-PG-DELAY</sub> V <sub>GATE</sub> High to Low Propagation Delay		C <sub>GATE</sub> = 1nF across GATE and SRC		84		ns
CURRENT SOU	RCE AT ADJ PIN					
I <sub>ADJ-STARTUP</sub>	Output Current of ADJ pin at Startup	V <sub>ADJ</sub> = 0V	16	20	24	μA
I <sub>ADJ-ELEC-XFR</sub>	Output Current of ADJ pin for Electronic Transformers	An Electronic Transformer is Detected	8	11.5	15	μΑ
I <sub>ADJ-MAG-XFR</sub> Output Current of ADJ pin for Inductive Air Transformers		An Magnetic Transformer is Detected	7	9.5	12	μA
CURRENT SEN	SE COMPARATOR					
V <sub>SEN-UPPER-TH</sub>	$V_{\rm SEN}$ Upper Threshold Over $V_{\rm ADJ}$	$V_{\text{SEN}}\text{-}V_{\text{ADJ}},$ $V_{\text{ADJ}}\text{=}0.2\text{V},$ $V_{\text{GATE}}$ at falling edge	8.9	14.9	20.9	mV
$V_{SEN-LOWER-TH}$	V <sub>SEN</sub> Lower Threshold Over VADJ	$V_{\text{SEN}}\text{-}V_{\text{ADJ}},$ $V_{\text{ADJ}}\text{=}0.2\text{V}$ $V_{\text{GATE}}$ at rising edge	-20.6	-14.9	-8.8	mV
V <sub>SEN-HYS</sub>	V <sub>SEN</sub> Hysteresis	(V <sub>SEN-UPPER-TH</sub> - V <sub>SEN-LOWER-TH</sub> )	22.5	29.8	37.5	mV
V <sub>SEN-OFFSET</sub>	V <sub>SEN</sub> Offset w.r.t. V <sub>ADJ</sub>	(V <sub>SEN-UPPER-TH</sub> + V <sub>SEN-LOWER-TH</sub> )/2	-3.5	0.02	3.5	mV
ACTIVE low-sid	e input rectifiers					
R <sub>ACn-ON</sub>	In resistance of AC1 and AC2 to GND	$I_{ACn} = 200 \text{mA}$		300	570	mΩ

(1) V<sub>CC</sub> provides self bias for the internal gate drive and control circuits. Device thermal limitations limit external loading.

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## **ELECTRICAL CHARACTERISTICS (continued)**

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	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>ACn-ON-TH</sub>	Turn ON Voltage Threshold of AC1 and AC2	DN Voltage Threshold of AC1 and V <sub>ACn</sub> Decreasing				
V <sub>ACn-OFF-TH</sub>	Turn OFF Voltage Threshold of AC1 and AC2	V <sub>ACn</sub> Increasing	77	90	104	mV
V <sub>ACn-TH-HYS</sub>	Hysteresis Voltage of AC1 and AC2	V <sub>ACn-OFF-TH</sub> - V <sub>ACn-ON-TH</sub>		39		mV
I <sub>ACn-OFF</sub>	Off Current of AC1 and AC2	V <sub>ACn</sub> = 45V		21	32	μA
OUTPUT OVER-	OLTAGE-PROTECTION (OVP)					
V <sub>ADJ-OVP-UPTH</sub>	Output Over-Voltage-Detection Upper Threshold	$V_{\text{ADJ}}$ Increasing, $V_{\text{GATE}}$ at falling edge	0.353	0.384	0.415	V
V <sub>ADJ-OVP-LOTH</sub>	Output Over-Voltage-Detection Lower Threshold	$V_{\text{ADJ}}$ Decreasing, $V_{\text{GATE}}$ at rising edge	0.312	0.339	0.366	V
V <sub>ADJ-OVP-HYS</sub>	Output Over-Voltage-Detection Hysteresis	V <sub>ADJ-OVP-UPTH</sub> - V <sub>ADJ-OVP-LOTH</sub>	25	46	67	mV
THERMAL SHUT	DOWN					
T <sub>SD</sub>	Thermal Shutdown Temperature	T <sub>J</sub> Rising		165		°C
T <sub>SD-HYS</sub>	Thermal Shutdown Temperature Hysteresis	T <sub>J</sub> Falling	30			°C



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#### **TYPICAL CHARACTERISTICS**

All curves taken for the boost circuit are with 500mA nominal input current and 6 serial LEDs. All curves taken for the SEPIC circuit are with 500mA nominal input current and 3 serial LEDs. $T_A = -40^{\circ}$ C to 125°C, unless otherwise specified.



Figure 1.











VCC UVLO Falling Threshold vs. Temperature V<sub>VP</sub>=12V, GATE='Low'





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### **OVERVIEW**

The TPS92560 is a simple hysteretic control switching LED driver for MR16 or AR111 lighting applications. The device accepts DC voltage, AC voltage and electronic transformer as an input power source. The compact application circuit can fit into a generic case of MR16 lamps easily. The hysteretic inductor current control scheme requires no small signal control loop compensation and maintains constant average input current to secure high compatibility to different kinds of input power source. The TPS92560 can be configured to either a step-up or step-up/down LED driver for the use of different number of LEDs. The patent pending current control mechanism allows the use of a single set of component and PCB layout for serving different output power requirements by changing the number of LEDs. The integrating of the active low-side input rectifiers reduces the power loss for voltage rectification and saves two external diodes of a generic bridge rectifier to aim for a simple end application circuit. When the driver is used with an AC voltage source or electronic transformer, the current regulation level increases accordingly to maintain an output current close to the level that when it is used with a DC voltage source. With the output over-voltage protection and over-temperature shutdown functions, the TPS92560 is specifically suitable for the applications that are space limited and need wide acceptance to different power sources.

### VCC REGULATOR

The VCC pin is the output of the internal linear regulator for providing an 8.45V typical supply voltage to the MOSFET driver and internal circuits. The output current of the VCC pin is limited to 30mA typical. A low ESR ceramic capacitor of  $0.47\mu$ F or higher capacitance should be connected across the VCC and SRC pins to supply transient current to the MOSFET driver.

### MOSFET DRIVER

The GATE pin is the output of the gate driver which referenced to the SRC pin. The gate driver is powered directly by the VCC regulator which the maximum gate driving current is limited to 30mA typical. To prevent hitting the VCC current limit, it is suggested to use a low gate charge MOSFET when high switching frequency is needed.

### THE ADJ PIN

The voltage on the ADJ pin determines the reference voltage for the input current regulation. Typically, the ADJ pin voltage is divided from the output voltage of the circuit by a voltage divider, thus the average input current is adjusted with respect to the number of LEDs used. The voltage of the ADJ pin determines the input current following the expression:

$$I_{\rm IN(nom)} = \frac{V_{\rm VP}}{R_{\rm SEN}} \times \frac{R_{\rm ADJ2}}{R_{\rm ADJ1} + R_{\rm ADJ2}}$$
(1)

### **Output Over-Voltage-Protection**

In the TPS92560, a function of output Over-Voltage Protection (OVP) is provided to prevent damaging of the circuit due to an open circuit of the LED. The OVP function is implemented to the ADJ pin. When the voltage of the ADJ pin exceeds 0.384V typical, the OVP circuit disables the MOSFET driver and turns off the main switch to allow the output capacitor to discharge. As the voltage of the ADJ pin decreases to below 0.353V typical, the MOSFET driver is enabled and the TPS92560 returns to normal operation. The triggering threshold of the output voltage is determined by the value of the resistors  $R_{ADJ1}$  and  $R_{ADJ2}$ , which can be calculated using the following equation:

$$V_{VP} \times \frac{R_{ADJ2}}{R_{ADJ1} + R_{ADJ2}} \le 0.384V$$
<sup>(2)</sup>

When defining the OVP threshold voltage, it is necessary to certain that the OVP threshold voltage does not exceed the rated voltage of the output rectifier and capacitor to avoid damaging of the circuit.

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The TPS92560 provides two internal active rectifiers for input voltage rectification. Each internal rectifier connects across the ACn pin to GND. These internal active rectifiers function as the low-side diode rectifiers of a generic bridge rectifier. The integrating of the active rectifiers helps in saving two external diodes of a bridge rectifier along with an improvement of power efficiency. For high power applications, for instance, 12W output power, external diode rectifiers can be added across the ACn pin to GND to reduce heat dissipation on the TPS92560.

V<sub>IN</sub> (From elect. transformer)

## **DETECTION OF POWER SOURCE**

 $12V \times \sqrt{2}$ 

Time 0 Switching period Dead time of the elect. transformer 1/50Hz or 1/60Hz -

Figure 13. The inherent dead time of the output voltage of an electronic transformer

Both the voltages of a generic AC source (50/60Hz) and an electronic transformer carry certain amount of dead time inherently, as shown in Figure 13. The existing of the dead time leads to a drop of the RMS input power to the driver circuit. In order to compensate the drop of the RMS input power, the ADJ pin sources current to the resistor, R<sub>AD12</sub> to increase the reference voltage for the current regulation loop and in turn increase the RMS input power accordingly when an AC voltage source or electronic transformer is detected. The output current of the ADJ pin for an AC input voltage and electronic transformer are 9.5µA and 11.5µA typical respectively. Practically the amount of the power for compensating the dead time of the input power source differs case to case depending on the characteristics of the power source, the value of the RADJ1 and RADJ2 might need a fine adjustment in accordance to the characteristics of the power source. The additional output power for compensating the dead time of the power sources ( $\Delta P_{LED}$ ) are calculated using the following equations:

#### For 50/60Hz AC power source:

$$\Delta P_{\text{LED}-50/60 \text{ Hz}} = V_{\text{IN}} \times \frac{R_{\text{ADJ2}} \times 9.5 \ \mu\text{A}}{R_{\text{SEN}}} \times \eta$$
(3)

For electronic transformer:

$$\Delta P_{\text{LED}-\text{ELECT}-\text{XFR}} = V_{\text{IN}} \times \frac{R_{\text{ADJ2}} \times 11.5 \ \mu\text{A}}{R_{\text{SEN}}} \times \eta$$
(4)

### **CURRENT REGULATION**

In the TPS92560, the input current regulation is attained by limiting the peak and valley of the inductor current. Practically the inductor current sensing is facilitated by detecting the voltage on the resistor, R<sub>SEN</sub>. Because the current flows through the R<sub>SEN</sub> is a sum total of the currents of the main switch and LEDs, the voltage drop on the R<sub>SEN</sub> reflects the current of the inductor that is identical to the input current to the LED driver circuit. Figure 14 shows the waveform of the inductor current ripple with the peak and valley values controlled.







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Figure 14. Inductor Current Ripple in Steady State

The voltage of the ADJ pin is determined by the forward voltage of the LED and divided from the  $V_{VP}$  by a resistor divider. The equation for calculating the  $V_{ADJ}$  as shown in the following expression:

$$V_{ADJ} = V_{VP} \times \frac{R_{ADJ2}}{R_{ADJ1} + R_{ADJ2}}$$
(5)

In steady state, the voltage drop on the  $R_{ADJ1}$  is identical to the forward voltage of the LED ( $V_{LED}$ ) and the voltage across the  $R_{ADJ2}$  is identical to the voltage across the  $R_{SEN}$ . The LED current,  $I_{LED}$  is then calculated following the equations:

In steady state:

$$V_{\text{LED}} = V_{\text{RADJ1}} \tag{6}$$

$$V_{\text{SEN}} = V_{\text{RADJ2}}$$
(7)  
$$I_{\text{IN}(\text{nom})} = \frac{V_{\text{SEN}}}{1}$$

$$_{\rm IN(nom)} = - \frac{1}{R_{\rm SEN}}$$
(8)

Since

 $P_{LED} = P_{IN} x \eta$  where  $\eta$  is the conversion efficiency

Thus,

 $V_{\text{LED}} \times I_{\text{LED}} = V_{\text{IN}} \times I_{\text{IN(nom)}} \times \eta$ (10)

Put the expressions (2) to (4) into (5):

$$I_{LED} = V_{IN} \times \frac{I_{ADJ2} \times R_{ADJ2}}{I_{ADJ1} \times R_{ADJ1} \times R_{SEN}} \times \eta$$
(11)

Due to the high input impedance of the ADJ pin, the current flows into the ADJ pin can be neglected and thus  $I_{RADJ1}$  equals  $I_{RADJ2}$ . The LED current is then calculated following the expressions below:

$$I_{LED} = V_{IN} x \frac{R_{ADJ2}}{R_{ADJ1} x R_{SEN}} x \eta$$
(12)

Practically, the conversion efficiency of a boost circuit is almost a constant around 85%. Being assumed that the efficiency term in the  $I_{LED}$  expression is a constant, the LED current depends solely on the magnitude of the input voltage,  $V_{IN}$ . Without changing a component, the output power of the typical application circuits of the TPS92560 is adjustable by using different number of LEDs.

The output power is calculated by following the expression:

$$P_{LED} = V_{LED} \times V_{IN} \times \frac{R_{ADJ2}}{R_{ADJ1} \times R_{SEN}} \times \eta$$
(13)

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(9)

### SWITCHING FREQUENCY (Boost Configuration)

In the following sections, the equations and calculations are limited to the boost configuration only (i.e. the LED forward voltage higher than the input voltage), unless otherwise specified. The application information for the SEPIC and other circuit topologies are available in separate application notes and reference designs. In the boost configuration, including the propagation delay of the control circuit, the ON and OFF times of the main switch are calculated following the expressions:

$$t_{ON} = \left\{ \frac{\left| V_{SEN-UPPER-TH} \right| \times L}{R_{SEN} \times \left[ V_{IN} - V_D - I_{IN(nom)} \times \left( R_L + R_{DS(ON)} + R_{SEN} + R_{AC-FET} \right) \right]} + t_{FALL-PG-DELAY} \right\} \times 2$$

$$t_{OFF} = \left\{ \frac{\left| V_{SEN-LOWER-TH} \right| \times L}{R_{SEN} \times \left[ V_{LED} - V_{IN} - 2V_D - I_{IN(nom)} \times \left( R_L + R_{SEN} + R_{AC-FET} \right) \right]} + t_{RISE-PG-DELAY} \right\} \times 2$$

$$(14)$$

In the above equations, the V<sub>D</sub> is the forward voltage of D<sub>3</sub>, R<sub>L</sub> is the DC resistance of L<sub>1</sub>, R<sub>DS(ON)</sub> is the ON resistance of Q<sub>1</sub> and R<sub>AC-FET</sub> is the turn ON resistance of the internal active rectifier with respect to the typical application circuit diagram.

Practically the resistance of the R<sub>L</sub>, R<sub>DS(on)</sub> and R<sub>AC-FET</sub> is in the order if serveral tenth of m $\Omega$ , by assuming a 0.5V diode forward voltage and the sum total of the R<sub>L</sub>, R<sub>DS(ON)</sub> and R<sub>AC-FET</sub> is close to 1 $\Omega$ , the on and off times of Q<sub>1</sub> can be approximated using the following equations:

$$t_{ON} \approx \left\{ \frac{14.9 \text{mV x L}}{\text{R}_{\text{SEN}} \text{ x } [\text{V}_{\text{IN}} - 0.5 \text{V} - \text{I}_{\text{IN}(\text{nom})} \text{ x } (1 + \text{R}_{\text{SEN}})]} + 84 \text{ns} \right\} \text{ x } 2$$

$$t_{OFF} \approx \left\{ \frac{14.9 \text{mV x L}}{\text{R}_{\text{SEN}} \text{ x } [\text{V}_{\text{LED}} - \text{V}_{\text{IN}} - 1 \text{V} - \text{I}_{\text{IN}(\text{nom})} \text{ x } (1 + \text{R}_{\text{SEN}})]} + 68 \text{ns} \right\} \text{ x } 2$$

$$(16)$$

$$(17)$$

With the switching on and OF times determined, the switching frequency can be calculated using the following equation:

$$f_{SW} = \frac{1}{t_{ON} + t_{OFF}}$$
(18)

Because of the using of hysteretic control scheme, the switching frequency of the TPS92560 in steady state is dependent on the input voltage, output voltage and inductance of the inductor. Generally a 1 MHz to 1.5 MHz switching frequency is suggested for applications using an electronic transformer as the power source.

### **INDUCTOR SELECTION (Boost Configuration)**

Because of the using of the hysteretic control scheme, the switching frequency of the TPS92560 in a boost configuration can be adjusted in accordance to the value of the inductor being used. Derived from the equations (12) and (13), the value of the inductor can be determined base on the desired switching frequence by using the following equation:

$$L = \frac{\left(\frac{1}{f_{SW}} - 304ns\right) \times R_{SEN}}{\left(\frac{1}{V_{IN} - 0.5V - I_{IN(nom)} \times (1 + R_{SEN})} + \frac{1}{V_{LED} - V_{IN} - 1V - I_{IN(nom)} \times (1 + R_{SEN})}\right) \times 29.8mV}$$
(19)

When selecting the inductor, it is essential to ensure the peak inductor current does not exceed the the factory suggested saturation current of the inductor. The values of the peak and valley inductor current are calculated using the following equations:

Peak inductor current:

$$I_{L(peak)} = \frac{[V_{IN} - V_D - I_{IN(nom)} \times (R_L + R_{DS(ON)} + R_{SEN} + R_{AC-FET})] \times t_{ON}}{2L} + I_{IN(nom)}$$
(20)

Valley inductor current:



$$I_{L(valley)} = I_{IN(nom)} - \frac{[V_{LED} - V_{IN} - 2V_{D} - I_{IN(nom)} x (R_{L} + R_{SEN} + R_{AC-FET})] x t_{OFF}}{2L}$$
(21)

Assume the total resistance of the R<sub>L</sub>, R<sub>DS(on)</sub> and R<sub>AC-FET</sub> is 1 $\Omega$  and the diode drop, V<sub>D</sub> equal to 1V, the peak and valley currents of the inductor can be approximated using the following equations:

$$I_{L(peak)} \approx \frac{[V_{IN} - 0.5V - I_{IN(nom)} \times (1 + R_{SEN})] \times t_{ON}}{2L} + I_{IN(nom)}$$
(22)  
$$I_{L(valley)} \approx I_{IN(nom)} - \frac{[V_{LED} - V_{IN} - 1V - I_{IN(nom)} \times (1 + R_{SEN})] \times t_{OFF}}{2L}$$
(23)

In order not to saturate the inductor, an inductor with a factory guranteed saturation current ( $I_{SAT}$ ) 20% higher than the  $I_{L(peak)}$  is suggested. Thus the  $I_{SAT}$  of the inductor should fulfill the following requirement:

 $I_{SAT} \ge I_{L(peak)} \times 1.2$ 

(24)

#### THERMAL SHUTDOWN

The TPS92560 includes a thermal shutdown circuitry that ceases the operation of the device to avoid permanent damage. The threshold for thermal shutdown is 165°C with a 30°C hysteresis typical. During thermal shutdown the VCC regulator is disabled and the MOSFET is turned off.

#### **INPUT SURGE VOLTAGE PROTECTION**

When use with an electronic transformer, the surge voltage across the input terminals can be sufficiently high to damage the TPS92560 depending on the charactistics of the electronic transformer. To against potential damaging due to the input surge voltage, a 36V zener diode can be connected across the input bridge rectifier as shown in Figure 15.



Figure 15. Input surge voltage protection using an external zener diode

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### EXAMPLE APPLICATION CIRCUITS

In the applications that need true regulation of the LED current, the intrinsic input current control loop can be changed to monitor the LED current by adding an external LED current sensing circuit. Figure 16 and Figure 19 show the example circuits for true LED current regulation in boost and SEPIC configurations respectively. In the circuits, the U<sub>3</sub> (TL431) maintains a constant 2.5V voltage drop on the resistors, R<sub>3</sub> and R<sub>7</sub>. Because the U<sub>2</sub> (TL431) maintains a constant voltage drop on the R<sub>3</sub>, the power dissipation on the output current sensing resistor, R<sub>7</sub> can be minimized by setting a low voltage drop on the R<sub>7</sub>. Because the change of the current flowing through the R<sub>7</sub> reflects in the change of the cathode current of U<sub>3</sub> and eventually adjusts the ADJ pin voltage of the TPS92560, the LED current is regulated independent of the change of the input voltage.

### **Boost Application Circuit with LED Current Regulation**

The specifications of the boost application circuit in Figure 16 are as listed below:

- Objective input voltage: 3VDC to 18VDC / 12VAC(50Hz or 60Hz) / Generic MR16 electronic transformer
- LED forward voltage: 20VDC typical
- Output current: 300mA typical (@12VDC input)
- Output power: 6W typical (@12VDC input)



Figure 16. Using the TPS92560 in SEPIC configuration with LED current regulation

### Typical Characteristics of the Boost Example Circuit in Figure 16

All curves taken at V<sub>IN</sub> = 3V to 18VDC in boost configuration, with 300mA nominal output current, 6 serial LEDs.  $T_A = 25^{\circ}C$ .





#### SEPIC Application Circuit with LED Current Regulation

The specifications of the SEPIC application circuit in Figure 16 are as listed below:

- Objective input voltage: 3VDC to 18VDC / 12VAC(50Hz or 60Hz) / Generic MR16 electronic transformer
- LED forward voltage: 13VDC typical
- Output current: 300mA typical (@12VDC input)
- Output power: 4W typical (@12VDC input)



Figure 19. Using the TPS92560 in SEPIC configuration with LED current regulation

### Typical Characteristics of the SEPIC Example Circuit in Figure 19

All curves taken at V<sub>IN</sub> = 3V to 18VDC in SEPIC configuration, with 300mA nominal output current, 4 serial LEDs.  $T_A = 25^{\circ}C$ .



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18



24-Jan-2013

### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing			(2)		(3)		(4)	
TPS92560DGQ/NOPB	ACTIVE	MSOP- PowerPAD	DGQ	10	1000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	SN3B	Samples
TPS92560DGQR/NOPB	ACTIVE	MSOP- PowerPAD	DGQ	10	3500	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	SN3B	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

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the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> Only one of markings shown within the brackets will appear on the physical device.

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